

ABSTRACT OF THE DISCLOSURE

A semiconductor memory device for reducing noise influence is disclosed. The device comprises an input circuit for receiving data to be written 5 into a memory cell array and outputting the received data to write buffer circuits that write the received data into the memory cell array; an output circuit for outputting read data to the outside, each of the read data elements having been read out 10 from the memory cell array and amplified by a corresponding sense amplifier; an input controller for controlling the input circuit so that the input circuit receives the received data only during a predetermined period; a plurality of input data 15 lines for transmitting the received data from the input circuit to the write buffer circuits; and a plurality of output data lines for transmitting the data amplified by the sense amplifiers to the output circuit. Each of the input data lines and each of 20 the output data lines are alternatingly and adjoiningly disposed on the semiconductor memory device.